

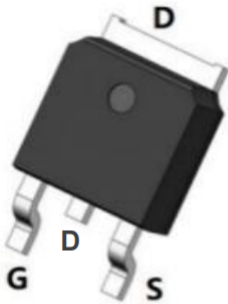
Product Summary

- V_{DS} 60 V
- I_{DS} 80A
- $R_{DS(ON)}$ (at $V_{GS}=10$) $\leq 6.6m\Omega$ (Typ)
- Low Gate Charge Minimize Switching Loss

Application

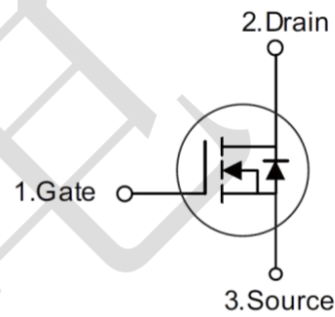
- Adaptor
- Charger
- Power management
- SMPS Standby Power

Package and Pin Configuration



TO-252

Circuit diagram



Absolute Maximum Ratings

($T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER	SYMBOL	Value	UNIT
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	80	A
Continuous Drain Current ($T_C=100^{\circ}C$)	I_D	56	A
Pulsed Drain Current (Note 1)	I_{DM}	240	A
Maximum Power Dissipation @ $T_A=25^{\circ}C$	P_D	68	W
Single Pulsed Avalanche Energy ⁽²⁾	E_{AS}	225	mJ
Operating Junction Temperature Range	T_J	+150	$^{\circ}C$
Storage Temperature Range	T_{stg}	-55 to +150	$^{\circ}C$

Note : 1.When mounted on 1" square PCB (FR4 material).

2. EAS condition: $T_J=25^{\circ}C$, $V_{DD}=30V$, $V_G=10V$, $L=0.5mH$, $R_g=25\Omega$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	BV_{DSS}	60	--	--	V
Gate-Source Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	$V_{GS(th)}$	1.2	1.7	2.2	V
Gate-Source Leakage	$V_{DS}=0V, V_{GS}= \pm 20V$	I_{GSS}	--	--	± 100	nA
Zero Gate Voltage Drain Current	$V_{DS}= 60V, V_{GS}=0V$	I_{DSS}	--	--	1	μA
Drain-Source On-State Resistance	$V_{GS}= 10V, I_D= 30A$	$R_{DS(on)}$	--	6.6	8.0	m Ω
	$V_{GS}= 4.5V, I_D= 30A$		--	9.3	11	
Forward Trans conductance	$V_{DS}=5V, I_D=30A$	g_{FS}	--	30	--	S
Dynamic (Note 2)						
Total Gate Charge (Note 3)	$V_{DS}= 30V,$ $I_D=20A,$ $V_{GS}= 10V$	Q_g	--	31	--	nC
Gate-Source Charge (Note 3)		Q_{gs}	--	6.0	--	
Gate-Drain Charge (Note 3)		Q_{gd}	--	5.0	--	
Input Capacitance	$V_{DS}= 30V, V_{GS}= 0V,$ $F= 1.0MHz$	C_{iss}	--	1990	--	pF
Output Capacitance		C_{oss}	--	470	--	
Reverse Transfer Capacitance		C_{rss}	--	14	--	
Switching						
Turn-On Delay Time (Note 3)	$V_{DD}= 30V,$ $I_D= 2A,$ $V_{GS}= 10V,$ $R_G= 3\Omega$	$t_{d(on)}$	--	16	--	nS
Rise Time (Note 3)		t_r	--	8.0	--	
Turn-Off Delay Time (Note 3)		$t_{d(off)}$	--	45	--	
Fall Time (Note 3)		t_f	--	33	--	
Source-Drain Diode Ratings and Characteristics (Note 2)						
Forward Voltage	$V_{GS}= 0V, I_S= 10A$	V_{SD}	--	0.8	1.2	V
Continuous Source Current	Integral reverse diode in the MOSFET	I_S	--	--	80	A
Pulsed Current (Note 1)		I_{SM}	--	--	240	A

Notes:

1. Pulse test; pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 1\%$.
2. Guaranteed by design, not subject to production testing.
3. Independent of operating temperature

TYPICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Fig. 1-Output Characteristics

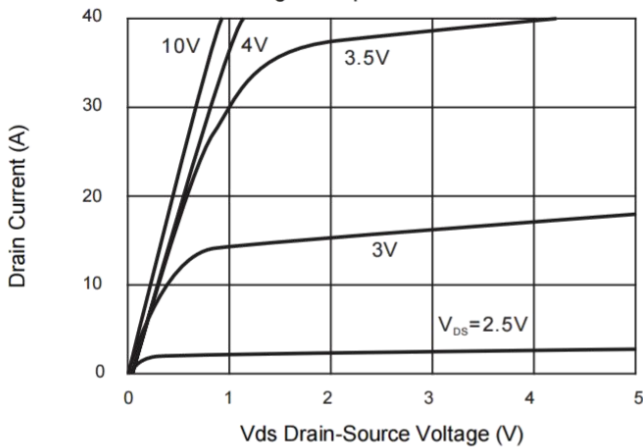


Fig. 2-Rdson-Junction Temperature

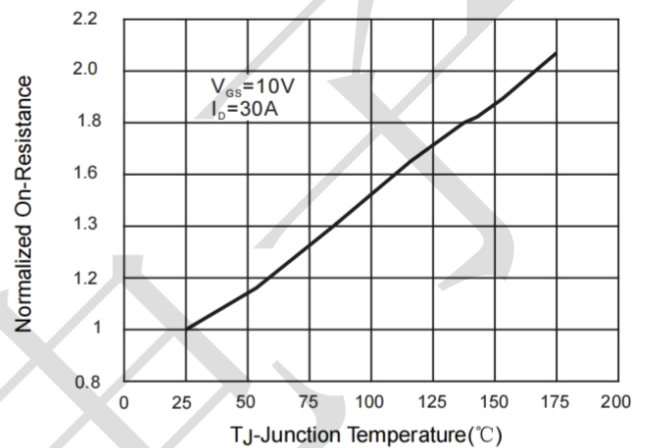


Fig. 3-Transfer Characteristics

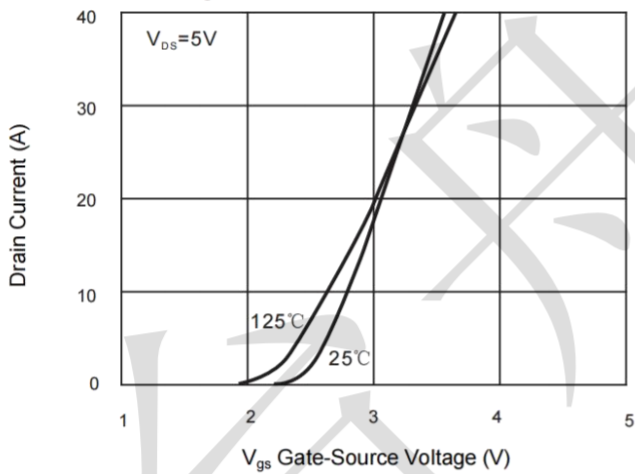


Fig. 4 - Total Gate Charge Characteristics

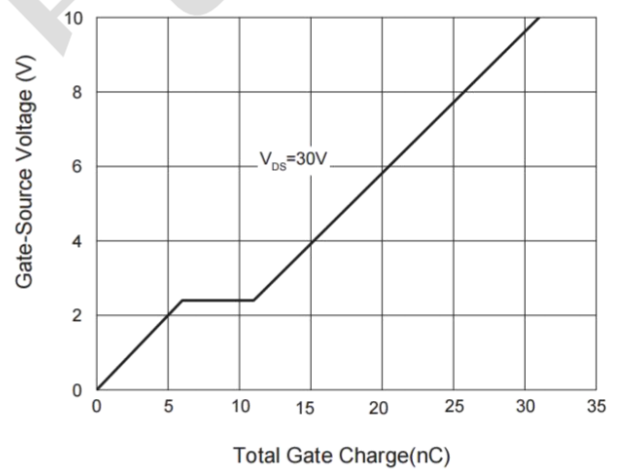


Fig. 5-Rdson- Drain Current

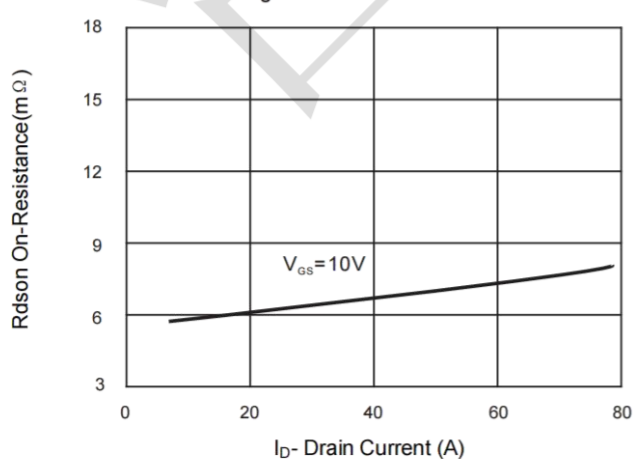
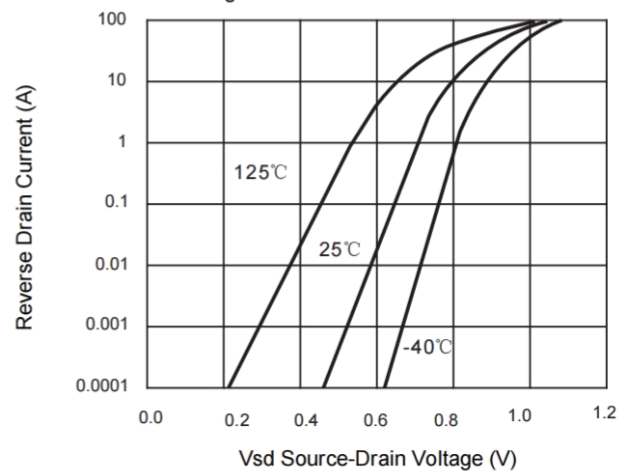
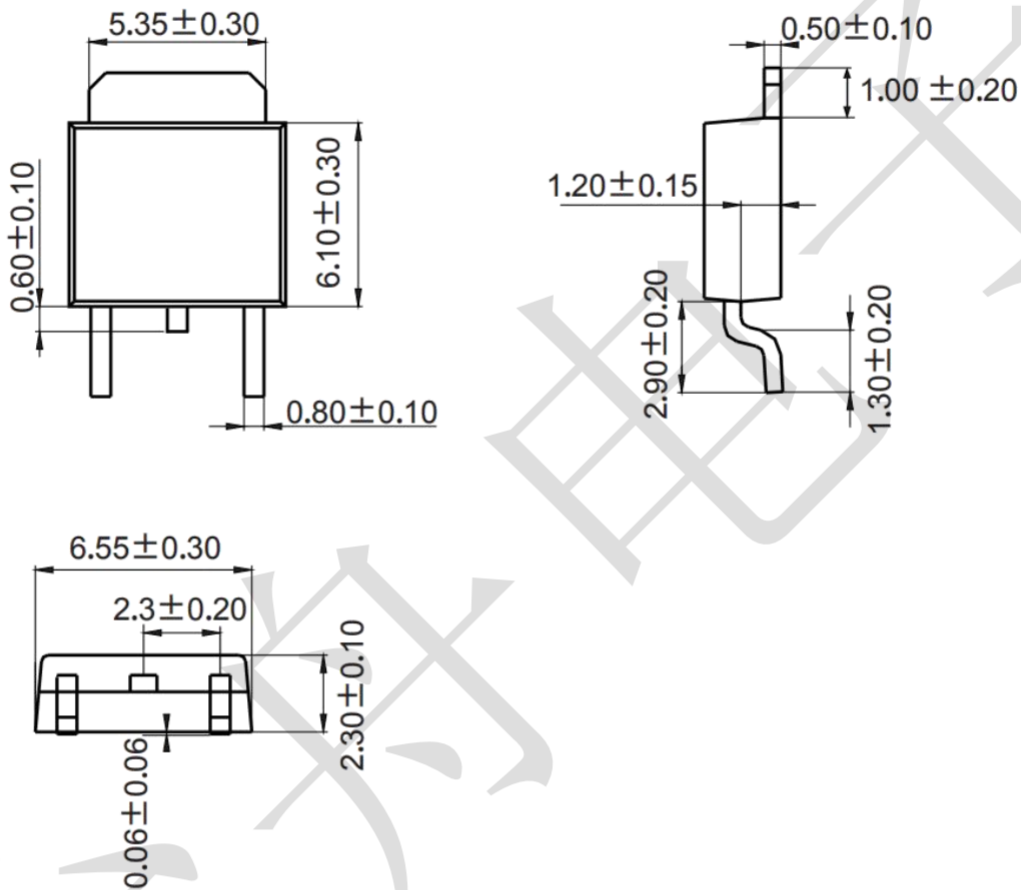


Fig. 6-Source- Drain Diode Forward



Package Outline Dimensions (unit: mm)

TO-252



Mounting Pad Layout (unit: mm)

